

interlayer insulating films formed on said main surface;  
conductive interconnections provided in a plurality of layers separated by said  
interlayer insulating films; and  
conductive dummy interconnections provided in the same layers as said  
interconnections in two or more layers included in said plurality of layers,  
wherein at least one of said dummy interconnections has repetitive protrusions and  
recesses along its elongate direction in a section taken along said main surface.

A1  
Amf  
11. (Amended) A semiconductor device comprising:  
a semiconductor substrate having a main surface along which a semiconductor  
element is formed;

interlayer insulating films formed on said main surface;  
conductive interconnections provided in a plurality of layers separated by said  
interlayer insulating films; and  
conductive dummy interconnections provided in the same layers as said  
interconnections in two or more layers included in said plurality of layers,  
wherein at least one of said dummy interconnections has repetitive protrusions and  
recesses along its elongate direction in a section taken along a plane perpendicular to said  
main surface.

---

Please add the following new claims:

---

21. The semiconductor device according to claim 10, wherein potentials  
corresponding to each of said lower-potential power-supply line or a higher-potential power-  
supply line are connected to said dummy conductive plug

A2  
22. The semiconductor device according to claim 10, comprising:  
a conductive dummy plug selectively buried in said interlayer insulating films to  
connect said dummy interconnections between said two or more layers and connected